

REMARKS

This application has been carefully reviewed in light of the Office Action dated July 31, 2002 (Paper No. 21). Claims 55 to 66 are in the application, with Claims 55, 65 and 66 being the independent claims. Reconsideration and further examination are respectfully requested.

Claims 11, 45 to 47 and 52 were rejected under 35 U.S.C. § 112, first paragraph, for alleged failure to satisfy the written description requirement; Claims 50 to 52 were rejected under 35 U.S.C. § 112, second paragraph; and Claims 11 to 20, 25 to 27, 30 to 32 and 45 to 54 were rejected under 35 U.S.C. § 103(a) over U.S. Patent No. 5,262,354 (Cote) in view of U.S. Patent No. 4,544,446 (Cady). In response, Claims 11 to 20, 25 to 27, 30 to 32 and 45 to 54 have been cancelled without prejudice or disclaimer of the subject matter presented therein and without conceding the correctness of their rejections, and new Claims 55 to 66 have been added, all of which are believed to be allowable.

More particularly, each of Claims 55 to 66 concerns fabrication of a semiconductor device in which an insulating film is formed on a substrate on which at least one switching element is formed. A portion of the insulating film is removed by an etching process to form a concave portion with the insulating film being removed. The concave portion results in a wiring pattern and contact holes. An electroconductive metal material is formed on the insulating film and in the concave portion. The metal material film is polished to remove the metal material formed on the insulating film. The surface of the substrate, including an upper surface of the polished metal material film and an upper face of the insulating film exposed by the polishing (or a reflective face), is washed. The

surface of the substrate is washed by means of an ultrasonic wave washing with a washing liquid to which an ultrasonic wave at a frequency band of not less than 800 kHz is applied, and is washed again by means of a scrubbing washing or a high-pressure jet washing.

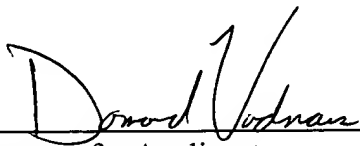
At least the foregoing features are not seen as disclosed by the Cote or Cady patents, and allowance of Claims 55 to 66 is therefore respectfully requested.

Turning to a formal matter, consideration of the art cited in the Information Disclosure Statement dated September 25, 2002 is respectfully requested. In addition, an Information Disclosure Statement is being submitted herewith, and the Examiner is respectfully requested to consider the art cited therein as well.

No other matters being raised, the entire application is believed to be in condition for allowance, and such action is courteously solicited.

Applicant's undersigned attorney may be reached in our Costa Mesa, California office at (714) 540-8700. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,



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